

IN THE CLAIMS

1. (Original) A memory device for use with a memory controller, the memory device comprising:
 - a memory cell array adapted to store internal depth data of an object; and
 - a data modifying circuit distinct from the memory controller, the data modifying circuit being adapted to
 - receive corresponding new external depth data of the object from the memory controller,
 - compare the new external depth data with the internal depth data, and
 - write the external depth data in the memory cell array over the internal depth data depending on the result of the comparison.
2. (Original) The memory device of claim 1, wherein the data modifying circuit is further adapted to output to the memory controller a status signal.
3. (Original) The memory device of claim 1, further comprising:
 - a first control pin for receiving a first control signal from the memory controller; and
 - a control circuit for transmitting the external depth data to the memory cell array thereby bypassing the data modifying circuit depending on a state of the first control signal.
4. (Original) The memory device of claim 3, wherein the data modifying circuit is further adapted to output to the memory controller a status signal.
5. (Original) The memory device of claim 4, wherein the status signal is output through the first control pin.
6. (Original) The memory device of claim 1, wherein the data modifying circuit includes
 - a register for storing the received new external depth data; and

a compare circuit for comparing the stored new external depth data with the internal depth data and for writing the external depth data in the memory cell array depending on the result of the comparison.

7. (Original) The memory device of claim 6, wherein the compare circuit is further adapted to write the external depth data in the memory cell array if the external depth data is smaller than the internal depth data.

8. (Original) The memory device of claim 6, wherein the compare circuit is further adapted to output a status signal to the memory controller.

9. (Original) The memory device of claim 6, further comprising:
a second control pin for receiving a second control signal from the memory controller,
wherein the compare circuit compares the internal depth data with the stored external depth data in units of X bits when the second control signal is in a non-active state, and in units of NX bits when the second control signal is in an active state.

10. (Original) The memory device of claim 9, wherein
if the second control pin is in an inactive state, the compare circuit outputs to the memory controller:
a first status signal indicating that the lower X bits of the internal depth data have been modified, and
a second status signal indicating that the upper X bits of the internal depth data have been modified.

11. (Original) The memory device of claim 9, wherein
if the second control pin is in a non-active state, the compare circuit outputs to the memory controller a status signal indicating that NX bits of the internal depth data have been modified.

12. (Previously presented) A method of processing depth data of an object in a memory device controlled by a memory controller, the method comprising:
receiving external depth data of the object from the memory controller;
storing the received external depth data;

receiving a first control signal from the memory controller through a first control pin distinct from the memory controller;

determining a state of the first control signal; and

if the state of the first control signal is determined to be inactive, writing the external depth data to a memory cell array within the memory device,

elseif the state of the first control signal is determined to be active, comparing the stored external depth data with corresponding internal depth data stored in the memory cell array, writing the external depth data over the corresponding internal depth data in the memory cell array depending on the result of the comparison, and outputting to the memory controller a status signal indicating that the internal depth data has been modified.

13. (Cancelled)

14. (Previously presented) The method of claim 12, wherein writing the external depth data takes place if the comparison yields that the external depth data is smaller than the internal depth data.

15. (Previously presented) The method of claim 12, wherein writing the external depth data takes place if the comparison yields that the external depth data is larger than the internal depth data.

16. (Previously presented) The method of claim 12, further comprising:
receiving a second control signal from the memory controller through a second control pin distinct from the memory controller;
determining a state of the second control signal; and
if the state of the second control signal is determined to be inactive, comparing the internal depth data with the stored external depth data in units of X bits,
elseif the state of the second control signal is determined to be active, comparing the internal depth data with the stored external depth data in units of NX bits.

17. (Previously presented) The method of claim 16, wherein comparing the internal depth data with the stored external depth data in units of X bits further includes outputting to the memory controller a first status signal indicating that the lower X bits of the internal depth data have been modified, and

outputting to the memory controller a second status signal indicating that the upper X bits of the internal depth data have been modified.

18. (Original) The method of claim 17, wherein the first status signal is output through the first control pin, and the second status signal is output through the second control pin.

19. (Previously presented) The method of claim 16, wherein comparing the internal depth data with the stored external depth data in units of NX bits further includes outputting to the memory controller a status signal indicating that the NX bits of the internal depth data has been modified.

20. (Original) The method of claim 19, wherein the status signal is output through one of the first and second control pins.

21. (Previously presented) A memory device for use with a memory controller, the memory device comprising:

- a memory cell array structured to store internal depth data of an object; and
- a data modifying circuit separate from the memory controller, the data modifying circuit structured to
 - receive corresponding new external depth data of the object from the memory controller,
 - compare the new external depth data to the internal depth data,
 - write the external depth data in the memory cell array over the internal depth data depending on the result of the comparison, and
 - output a status signal to the memory controller.

22. (Previously presented) A memory device for use with a memory controller, the memory device comprising:

- a memory cell array structured to store internal depth data of an object;
- a first control pin for receiving a first control signal from the memory controller;
- a data modifying circuit separate from the memory controller, the data modifying circuit structured to:

receive corresponding new external depth data of the object from the memory controller,

compare the new external depth data to the internal depth data,

write the external depth data in the memory cell array over the internal depth

data depending on the result of the comparison, and

output to the memory controller a status signal; and

a control circuit for transmitting the external depth data to the memory cell array

separate from the data modifying circuit, depending on a state of the first control signal.

23. (Previously presented) The memory device of claim 22, wherein the status signal is output through the first control pin.